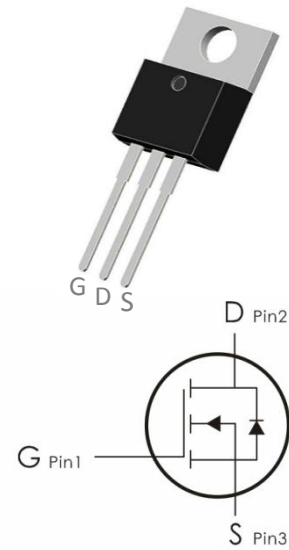


Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=30V, I_D=150A, R_{DS(ON)}<3m\Omega, @V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ C$	150	A
	Continuous Drain Current- $T_C=100^\circ C$	98	
I_{DM}	Pulsed Drain Current ¹	600	A
E_{AS}	Single Pulse Avalanche Energy ²	225	mJ
P_D	Power Dissipation- $T_J=25^\circ C$	109	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.4	$^\circ C/W$

Package Marking and Ordering Information:

Part NO.	Marking	Package
DOP150N03	150N03	TO-220

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=30V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	1	1.6	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance ³	$V_{GS}=10V, I_D=30A$	---	2.3	3	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$	---	4.2	6	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	3498	---	μF
C_{oss}	Output Capacitance		---	499	---	
C_{rss}	Reverse Transfer Capacitance		---	430	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, I_D=30A,$ $R_G=3\ \Omega, V_{GS}=10V$	---	25	---	ns
t_r	Rise Time		---	24	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	90	---	ns
t_f	Fall Time		---	38	---	ns
Q_g	Total Gate Charge	$V_{GS}=10V, V_{DS}=15V,$ $I_D=30A$	---	37	---	nC
Q_{gs}	Gate-Source Charge		---	8	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	12	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$I_D=30A$	---	---	1.2	V
I_S	Continuous Source Current	$V_G=V_D=0V$	---	---	150	A

I_{SM}	Pulsed Source Current	V _G =V _D =0V	---	---	600	A
T_{rr}	Reverse Recovery Time	I _S =20A, V _{GS} =0V	---	42	---	ns
Q_{rr}	Reverse Recovery Charge	diF/dt=100A/μs	---	39	---	μc

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: T_J=25°C, V_D=15V, V_G=10V, R_G=25Ω, L=0.5mH, I_{AS}=30A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristics: (T_c=25°C unless otherwise noted)

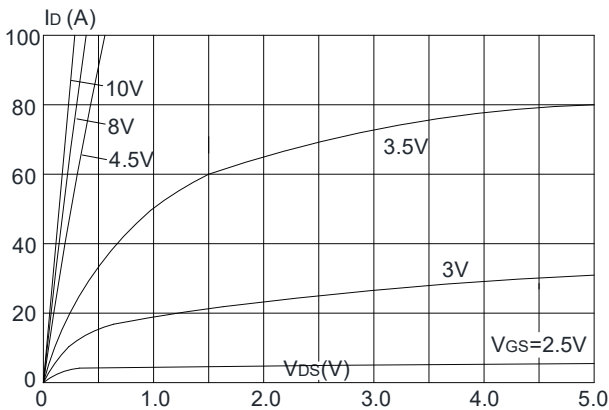


Figure 1: Output Characteristics

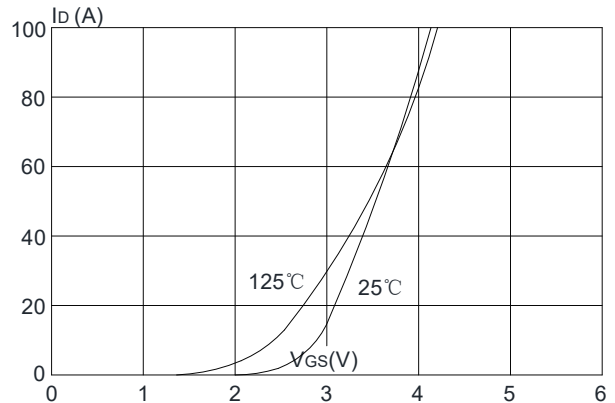


Figure 2: Typical Transfer Characteristics

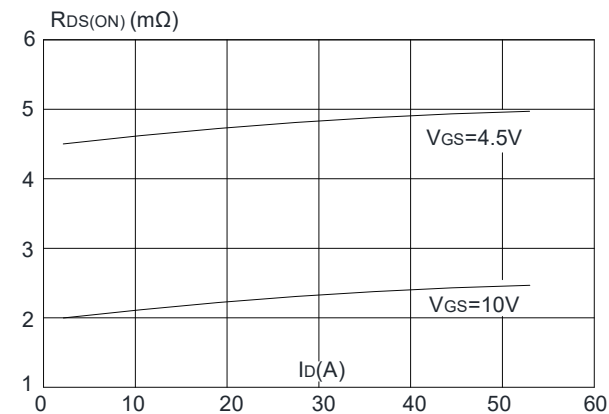


Figure 3: On-resistance vs. Drain Current

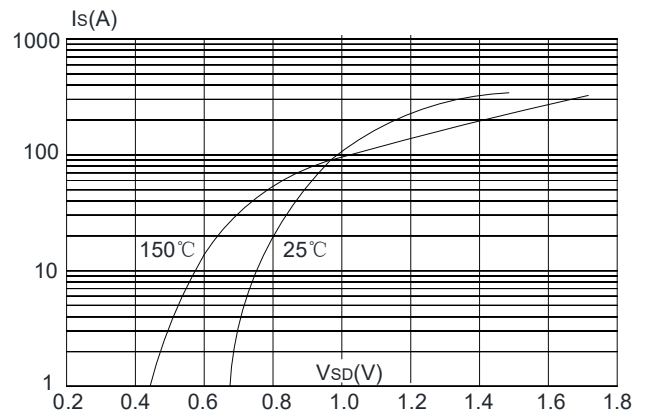


Figure 4: Body Diode Characteristics

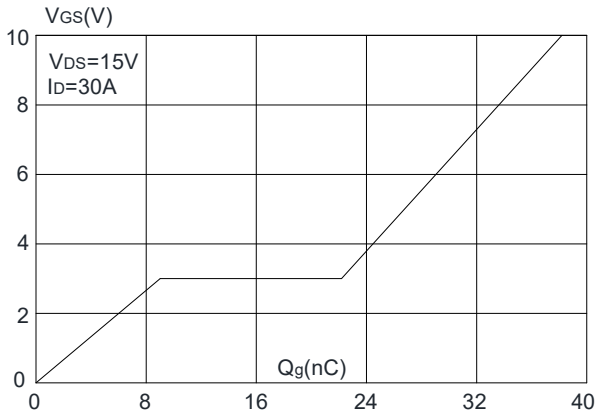


Figure 5: Gate Charge Characteristics

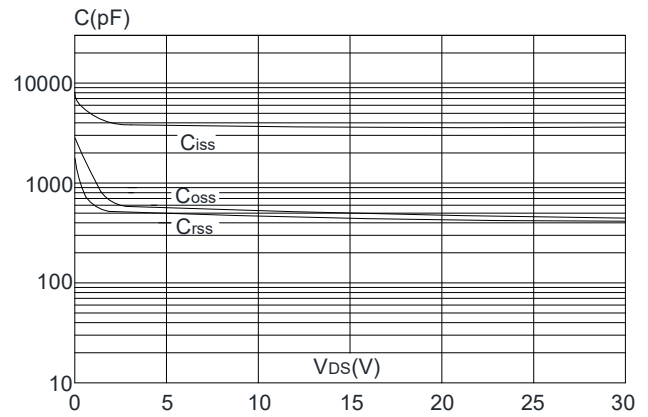


Figure 6: Capacitance Characteristics

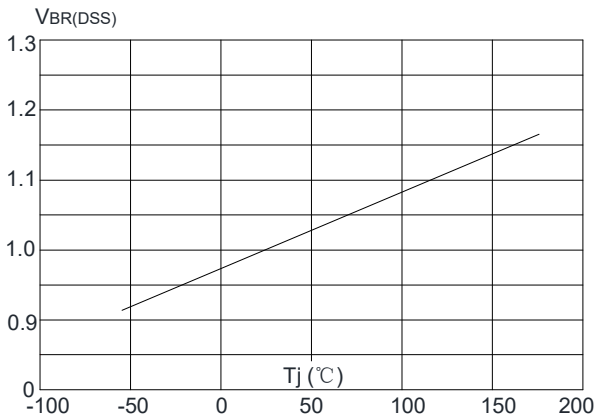


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

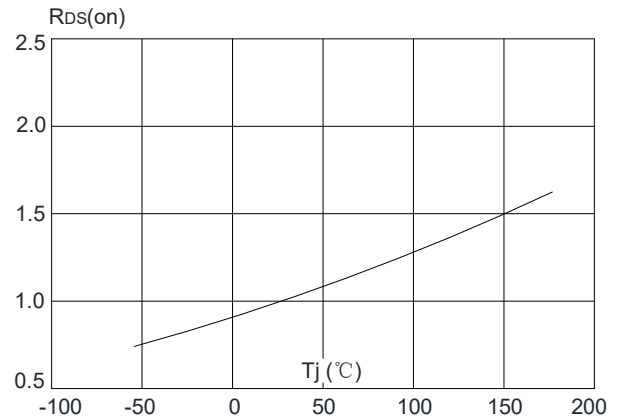


Figure 8: Normalized on Resistance vs. Junction Temperature

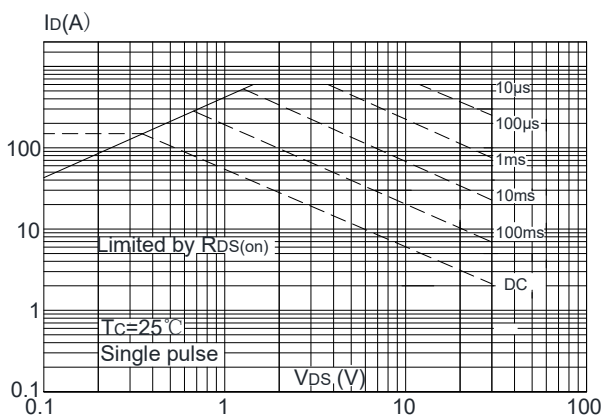


Figure 9: Maximum Safe Operating Area

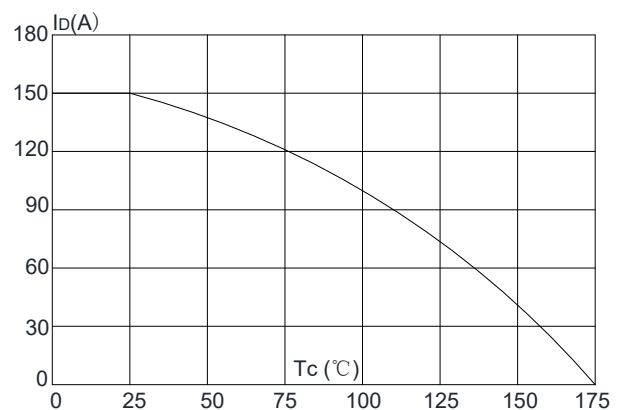


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

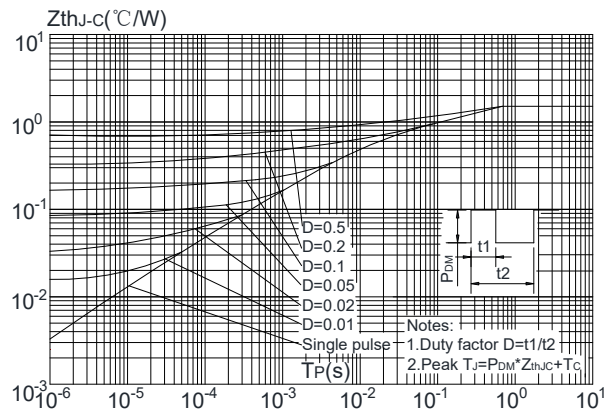


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case